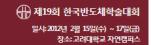
Semiconductor for Smart Living Technologies

The 19th Korean Conference on Semiconductors



G. Device & Process Modeling, Simulation and Reliability 분과

Room G

하나스퀘어 (B112)

일 시:2월 17일(금) 11:20-12:35

세션명: [FG2-G] Modeling and Simulation II

좌 장: 황성보(매그나칩반도체), 이정수(포항공과대학교)

FG2-G-1 11:20-11:50 [Invited] Full Quantum-mechanical Calculation of Gate Leakage

Current in Nano-scale MOSFETs

저자: Mincheol Shin, Kihoon Park, and Jung Hyun Oh 소속: Department of Electrical Engineering, KAIST

FG2-G-2 11:50-12:05 Estimation of Initial Surface Potential and Modeling of Inversion

Charge for Double-Gate MOSFET

저자: 황병운¹, 이창용², 이석희¹, 양지운²

소속: ¹Department of Electrical Engineering, KAIST, ²Department of

Electronics and Information Engineering, Korea University

FG2-G-3 12:05-12:20 Non-equilibrium Green's Function Approach to Surface-roughness-

limited Mobility in Silicon Nanowire Field Effect Transistors

저자: Hyo-Eun Jung and Mincheol Shin

소속: Department of Electrical Engineering, KAIST

FG2-G-4 12:20-12:35 Study of Hole-mobility Behaviors in Ultra-scaled Silicon Nanowire

Field Effect Transistors: Multi-band Monte Carlo Approach

저자: Hoon Ryu¹, Ju-Young Jung², and Mincheol Shin²

소속: ¹Supercomputing Center, Korea Institute of Science and Technology Information, ²Department of Electrical Engineering,

KAIST